



#### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

200 mA

#### **Features**

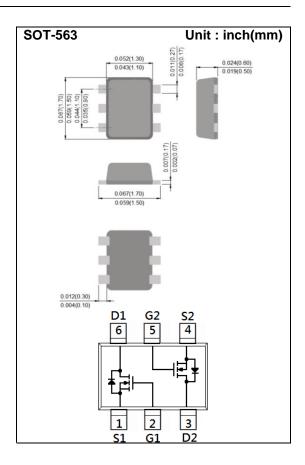
- RDS(ON), VGS@10V, ID@600mA<3Ω
- RDS(ON), VGS@4.5V, ID@200mA<4Ω
- Advanced Trench Process Technology
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: SOT-563 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0026 grams



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 30	V
Continuous Drain Current		I <sub>D</sub>	200	mA
Pulsed Drain Current		I <sub>DM</sub>	800	mA
Power Dissipation	T <sub>A</sub> =25°C	1	300	mW
	Derate above 25°C	P <sub>D</sub>	4	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>θJA</sub>	417	°C/W





### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0	1.8	2.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =600mA	-	1.3	3	Ω	
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =200mA	-	1.7	4		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 30V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic <sup>(Note 4)</sup>							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =15V, I <sub>D</sub> =600mA, V <sub>GS</sub> =4.5V	-	0.82	-	nC	
Gate-Source Charge	$Q_gs$		-	0.53	-		
Gate-Drain Charge	$Q_gd$		-	0.22	-		
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	34	-	pF	
Output Capacitance	Coss		-	11	-		
Reverse Transfer Capacitance	Crss		-	3.0	-		
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}=10V, I_{D}=600mA,$ $V_{GS}=10V,$ $R_{G}=6\Omega^{(Note 1,2)}$	-	2.7	-	ns	
Turn-On Rise Time	tr		-	21	-		
Turn-Off Delay Time	td <sub>(off)</sub>		-	3.8	-		
Turn-Off Fall Time	tf	KG=012(1000 1,2)	-	18	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	500	mA	
Diode Forward Current	Is						
Diode Forward Voltage	V <sub>SD</sub>	Is=500mA, V <sub>GS</sub> =0V	-	0.9	1.5	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
- 4. Guaranteed by design, not subject to production testing





#### **TYPICAL CHARACTERISTIC CURVES**

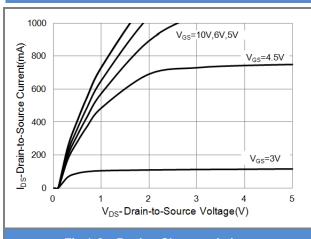
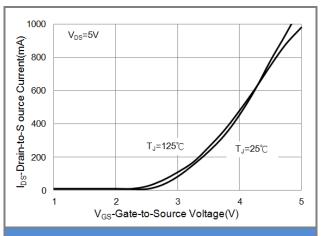


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

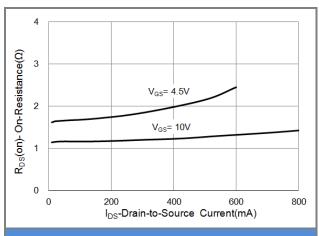


Fig.3 On-Resistance vs. Drain Current

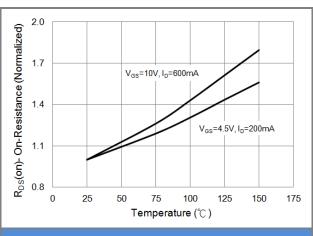
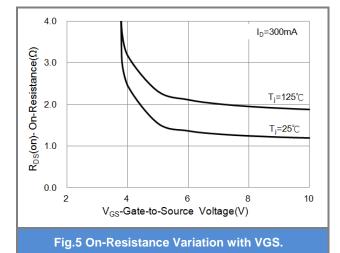
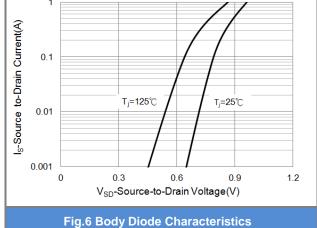


Fig.4 On-Resistance vs. Junction temperature







1.5

1.2

Vth-G-S Variance 6.0 9.0

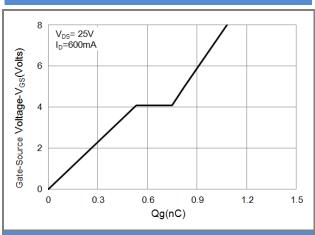
0.3

0



## **PJX8872B**

#### **TYPICAL CHARACTERISTIC CURVES**



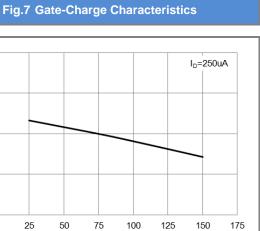


Fig.9 Threshold Voltage Variation with Temperature.

Temperature (°C)

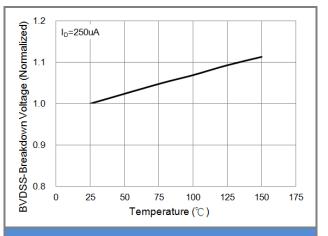


Fig.8 Breakdown Voltage Variation vs. Temperature

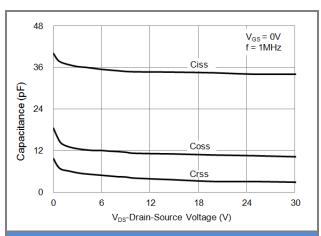


Fig.10 Capacitance vs. Drain-Source Voltage.

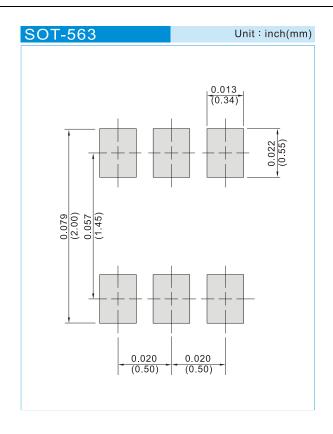




### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJX8872B_R1_00001	SOT-563	4K pcs / 7" reel	X2B	Halogen free RoHS compliant
PJX8872B_R2_00001	SOT-563	10K pcs / 13" reel	X2B	Halogen free RoHS compliant

### **Mounting Pad Layout**







#### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
  responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
  representation or warranty that such applications will be suitable for the specified use without further testing or
  modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.